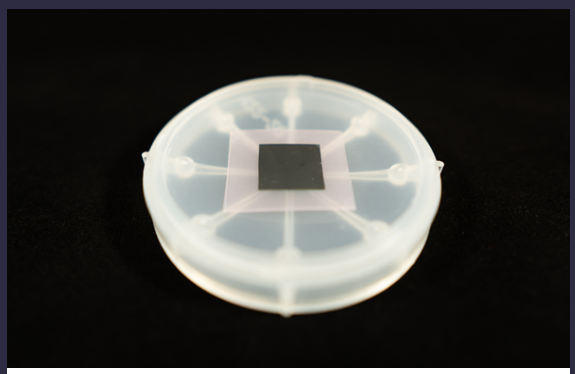
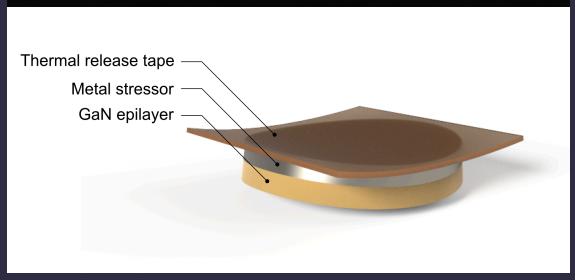
Free standing GaN

Future Semiconductor Business

FSB free standing GaN by **Remote Epitaxy and 2 Dimensional Material based Layer Transfer (2DLT)** provides a large area and high-quality single crystalline GaN epi-wafer for solution of high performance power and RF devices.

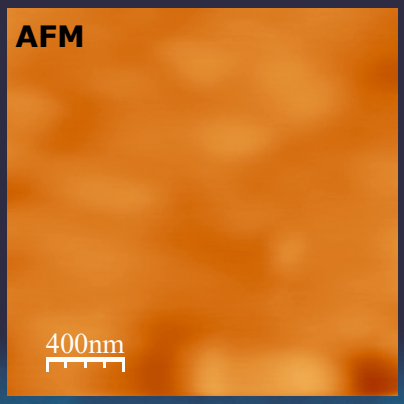


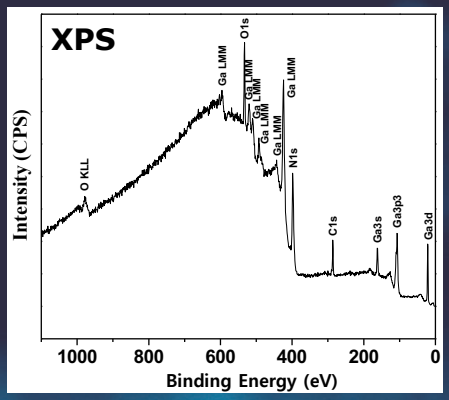


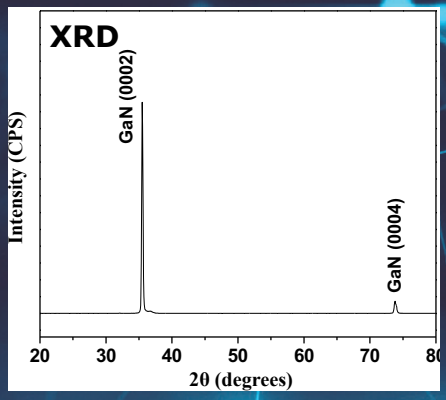
GaN/Ni/thermal release tape

MBE or MOCVD based free standing GaN can provide merits as follows;

- Large scale GaN epi-wafer
- High-quality GaN epi-wafer
- Production cost reduction due to low cost GaN epilayer







Conduction Type	N-type (Undoped)	N-type (Si-doped)	P-type	Semi-insulating
Structure	GaN/Ni/thermal release tape			
Orientation	c-axis (00.1) ± 1.0°	c-axis (00.1) ± 1.0°	c-axis (00.1) ± 1.0°	c-axis (00.1) ± 1.0°
Available Sizes	1 cm x 1 cm 5.08 cm diameter	1 cm x 1 cm 5.08 cm diameter	1 cm x 1 cm 5.08 cm diameter	1 cm x 1 cm 5.08 cm diameter
Useable Surface Area	≥ 90 %	≥ 90 %	≥ 90 %	≥ 90 %
Surface Finish	< 0.6 nm RMS	< 0.6 nm RMS	< 0.6 nm RMS	< 0.6 nm RMS

Other thickness and size options available upon request

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